

BACK-END

MOS-FET

IGBT

CAPACITY TEST SYSTEM 容量測定器

CPS3000 3000V

NEW

- By increasing the applied voltage of the CPS series to 3000V, it has become possible to perform measurements that are useful for developing high breakdown voltage devices.
- CPS シリーズの印加電圧を 3000V までアップし、高耐圧素子の開発に役立つ測定が可能です。



Note) The HEAD BOX on the right side of the photo is different from the actual one.
 注) 写真右側の HEAD BOX は実物と異なります。

MODEL	CPS3000
MEASURABLE ITEMS	MOS-FET, IGBT : Ciss, Coss(GD), Coss, Crss, CissV-, Rg : Cgc = Crss : Cge = Ciss-Crss : Cce = Coss-(Cgc x Cge)/(Cgc+Cge)
VCE	+ 00.1V ~ + 99.9V(+ 0.1V STEP) + 001V ~ + 999V(+ 1V STEP) + 0.01kV ~ + 3.00kV(+ 0.01kV STEP)
LOWER GATE/UPPER GATE	000.0pF ~ 999.9nF
CAPACITANCE MEASUREMENT	100pF ~ 999.9nF(100kHz ~ 1MHz, [with some conditions] 一部条件付き)
MEASUREMENT TIME	10ms ~ 999ms
DIMENSIONS & WEIGHT	
MAIN UNIT	430(W) x 700(D) x 245(H) ... 28kg
HEAD BOX	430(W) x 440(D) x 245(H) ... 15kg